2SC5225

Silicon NPN Epitaxial Transistor

HITACHI

ADE-208-393

Application

- Wide band video output amplifier for color CRT monitor.
- High frequency high voltage amplifier.
- High speed power switching.
- Complementary pair with 2SA1960.

Features

• High voltage large current operation.

$$V_{CEO} = 80 \text{ V}, I_{C} = 300 \text{ mA}$$

• High f_T.

$$f_T = 1.4 \text{ GHz}$$

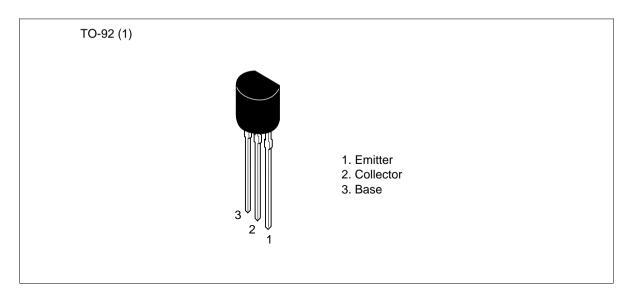
• Small output capacitance.

$$Cob = 3 pF$$



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Outline

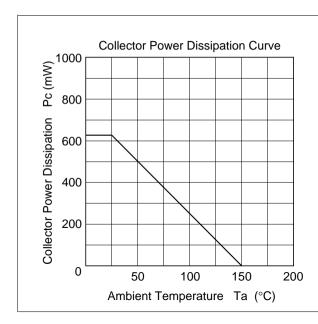


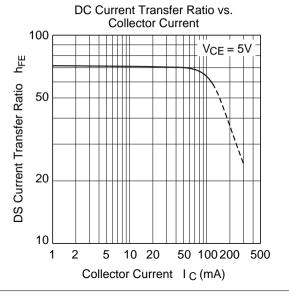
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

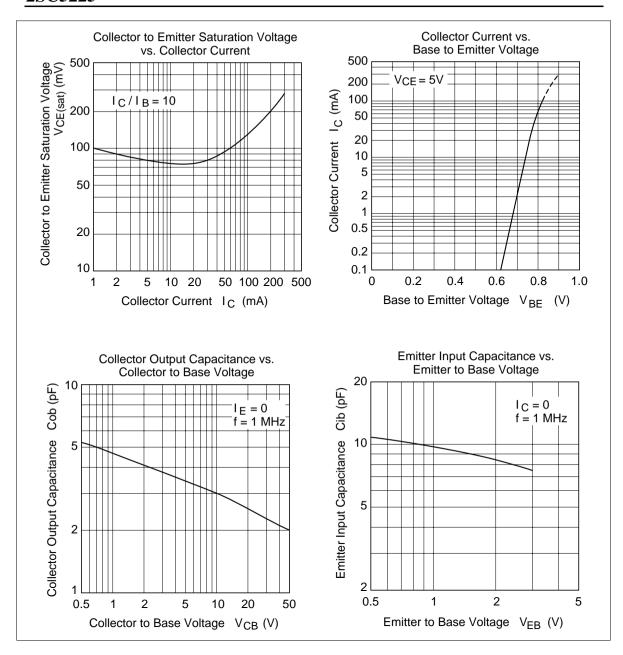
Item	Symbol	Ratings	Unit	
Collector to base voltage	V_{CBO}	100	V	,
Collector to emitter voltage	V _{CEO}	80	V	
Emitter to base voltage	V_{EBO}	3	V	
Collector current	I _c	300	mA	
Collector power dissipation	P _c	625	mW	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

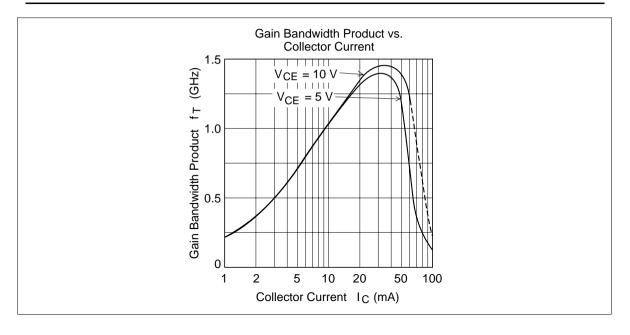
Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{\text{(BR)CBO}}$	100	_	_	V	$I_{c} = 100 \ \mu\text{A}, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	80	_	_	V	$I_{C} = 1 \text{ mA}, R_{BE} = \infty$
Collector to base cutoff current	I _{CBO}	_	_	1	μΑ	$V_{CB} = 80 \text{ V}, I_{E} = 0$
Emitter to base cutoff current	I _{EBO}	_	_	10	μΑ	$V_{EB} = 3 \text{ V}, I_{C} = 0$
DC current transfer ratio	h _{FE}	20	70	_		$V_{CE} = 5 \text{ V}, I_{C} = 50 \text{ mA}$ Pulse test
Gain bandwidth product	f _T	1.2	1.4	_	GHz	$V_{CE} = 10 \text{ V}, I_{C} = 50 \text{ mA}$
Emitter input capacitance	Cib	_	13	19	pF	$V_{EB} = 0, I_{C} = 0, f = 1 \text{ MHz}$
Collector output capacitance	Cob	_	3	4	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$

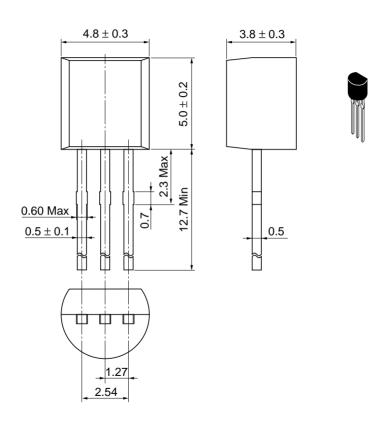








Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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